

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	12	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	5.6 4.4	A
	t < 5s	T _A = +25°C T _A = +70°C	I _D	7.2 5.8	A
Maximum Continuous Body Diode Forward Current (Note 5)			I _S	1	A
Pulsed Drain Current (10μs pulse, Duty Cycle = 1%)			I _{DM}	20	A
Avalanche Current (L = 0.1mH)			I _{AS}	15	A
Avalanche Energy (L = 0.1mH)			E _{AS}	12	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	P _D	1.4	W
	t < 5s		2.2	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	91	°C/W
	t < 5s		55	
Thermal Resistance, Junction to Case		R _{θJC}	20	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	12	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	μA	V _{DS} = 12V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	0.4	—	1	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	17	29	mΩ	V _{GS} = 4.5V, I _D = 5A
		—	20	34		V _{GS} = 2.5V, I _D = 4.6A
		—	24	44		V _{GS} = 1.8V, I _D = 4.1A
		—	30	65		V _{GS} = 1.5V, I _D = 2A
Diode Forward Voltage	V _{SD}	—	0.6	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	914	—	pF	V _{DS} = 6V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	132	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	119	—	pF	
Gate Resistance	R _g	—	1.26	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	10.5	—	nC	
Total Gate Charge (V _{GS} = 8V)		—	19.6	—	nC	
Gate-Source Charge	Q _{gs}	—	1.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.6	—	nC	V _{DD} = 6V, V _{GS} = 4.5V, R _L = 1.2Ω, R _G = 1Ω
Turn-On Delay Time	t _{D(ON)}	—	5.0	—	ns	
Turn-On Rise Time	t _R	—	10.5	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	16.6	—	ns	
Turn-Off Fall Time	t _F	—	4.1	—	ns	

- Notes:
- Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

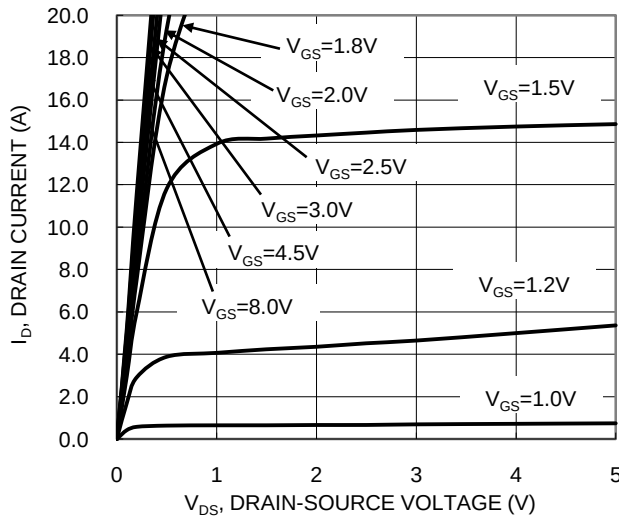


Figure 1. Typical Output Characteristic

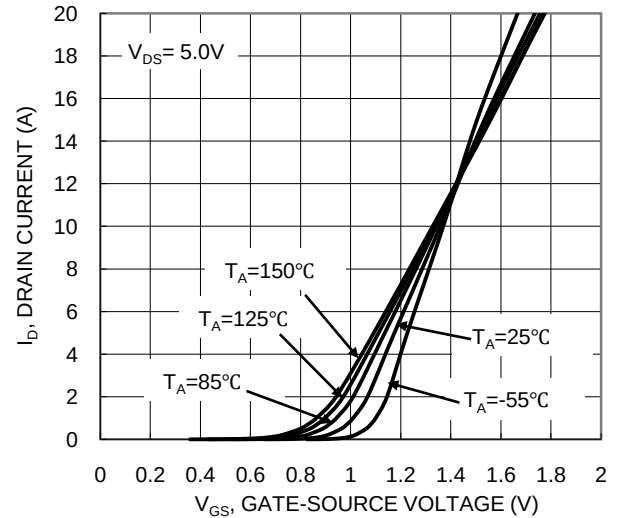


Figure 2. Typical Transfer Characteristic

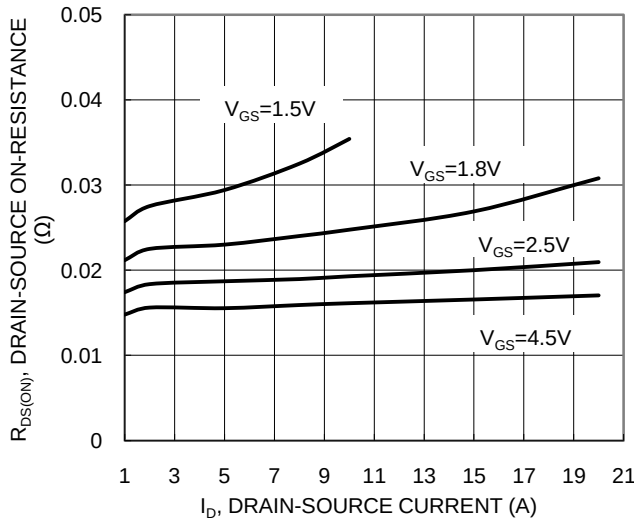


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

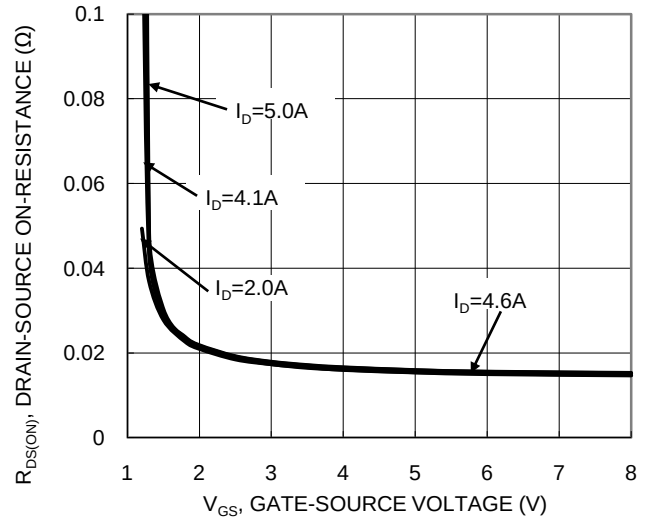


Figure 4. Typical Transfer Characteristic

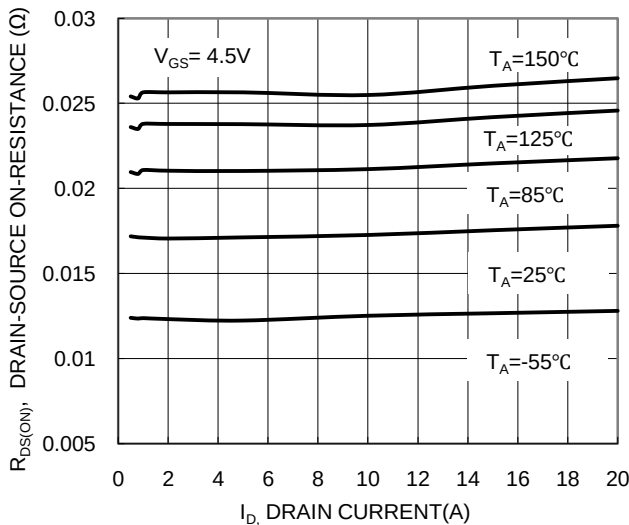


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

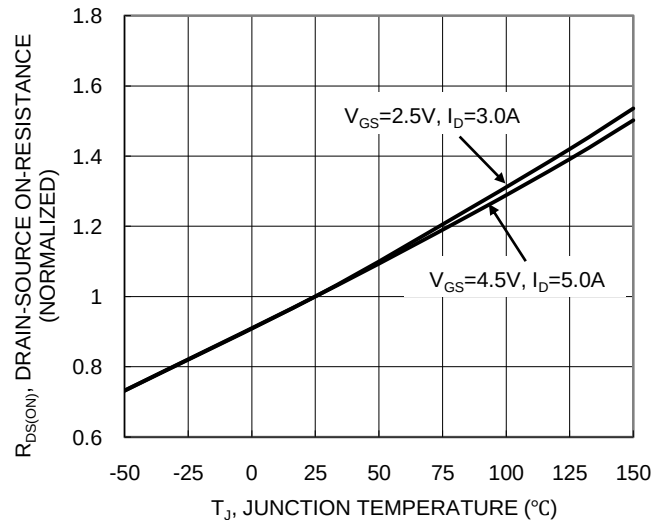
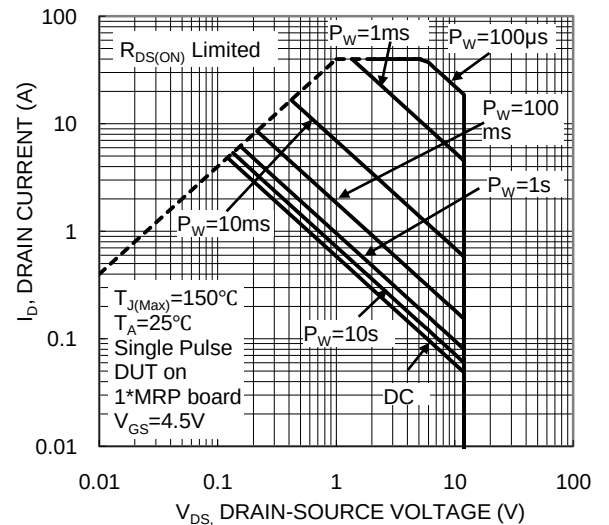
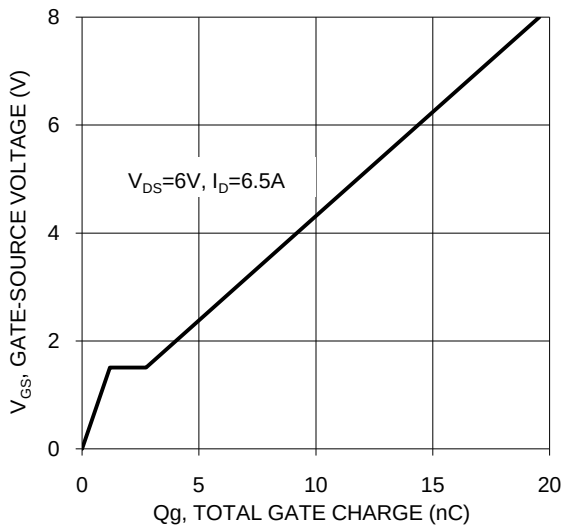
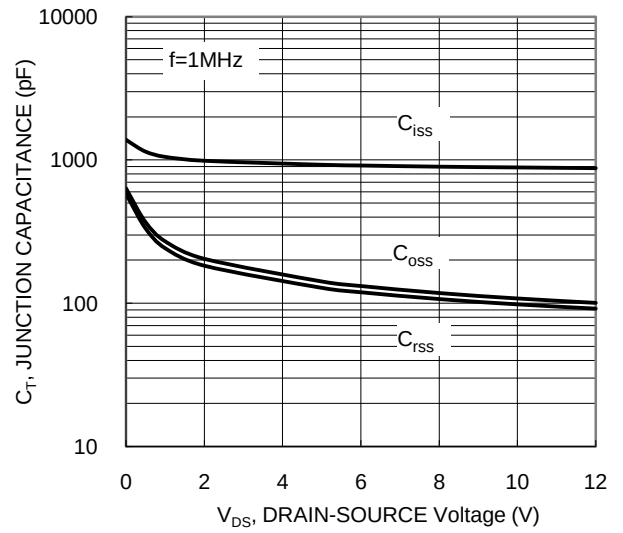
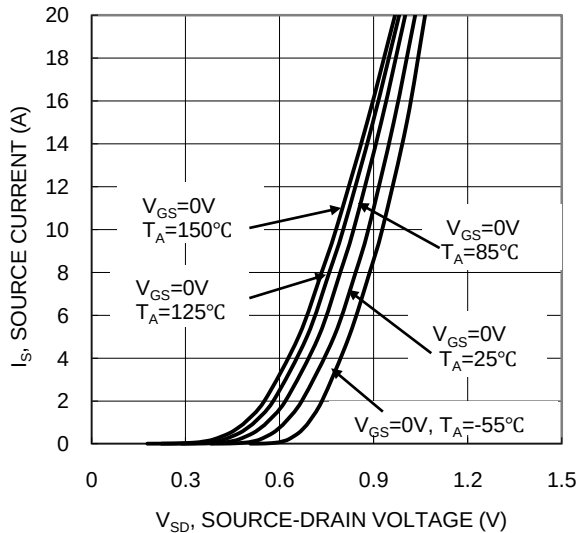
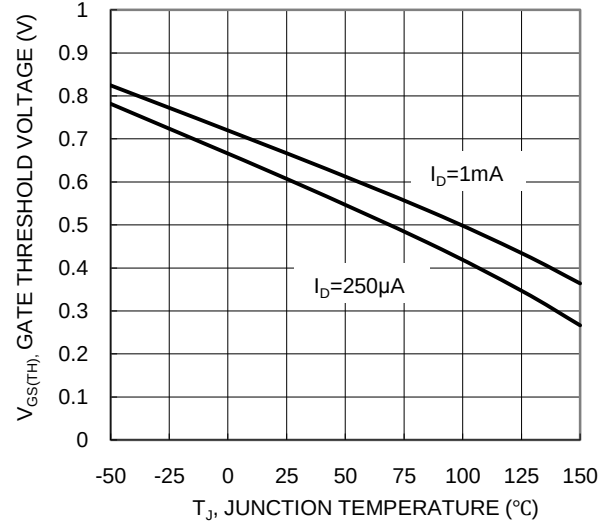
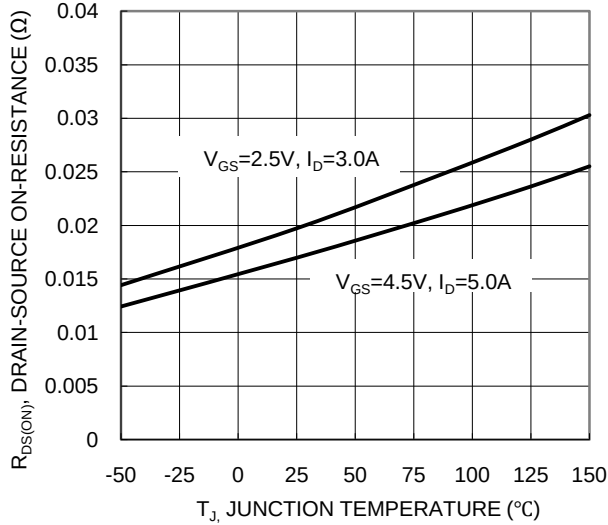
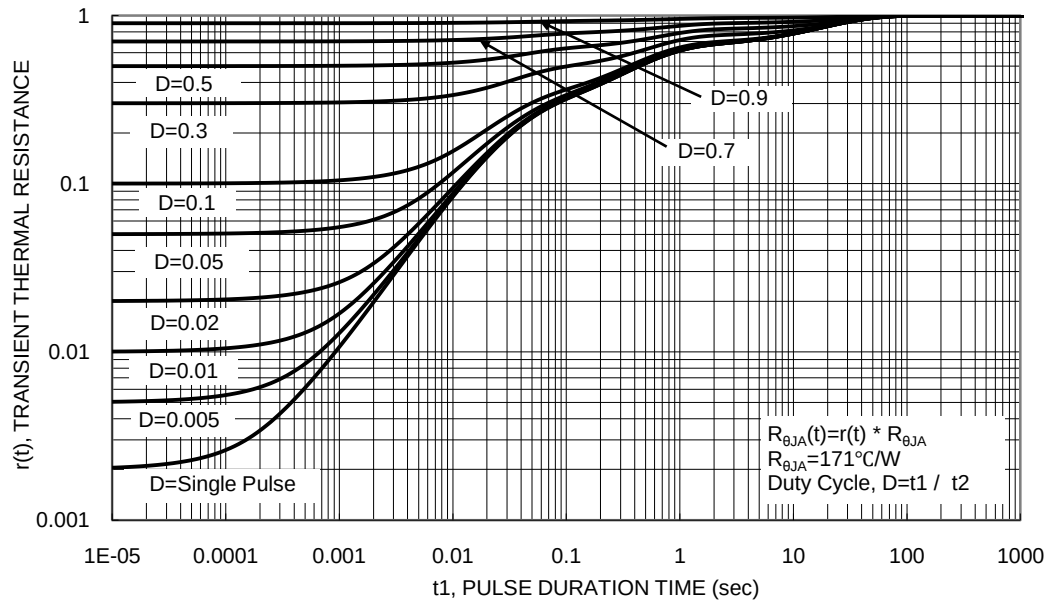


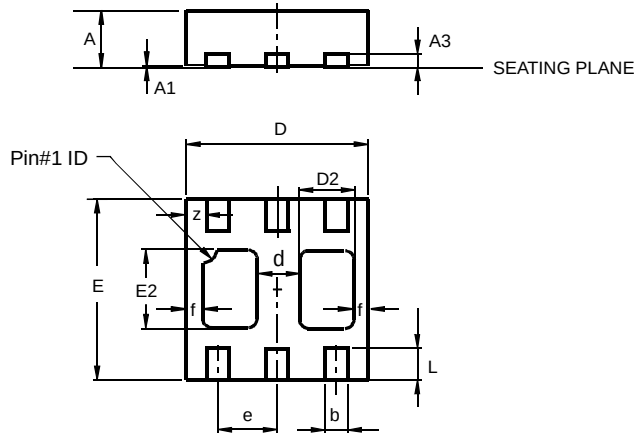
Figure 6. On-Resistance Variation with Temperature





Package Outline Dimensions

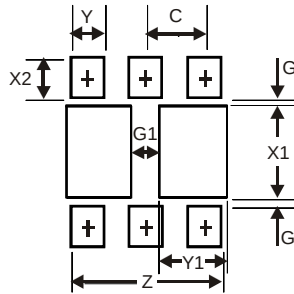
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



U-DFN2020-6 Type B			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0	0.05	0.02
A3	—	—	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
d	—	—	0.45
D2	0.50	0.70	0.60
e	—	—	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
f	—	—	0.15
L	0.25	0.35	0.30
z	—	—	0.225
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Y	0.37
Y1	0.70
C	0.65

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

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moschip.ru_9